Small-Signal Field Effect Transistor

N–Channel Enhancement Mode Silicon Gate TMOS

... are designed for high voltage, high speed applications such as switching regulators, converters, solenoid, and relay drivers.

- Silicon Gate for Fast Switching Speeds
- Relay Driver
- Telecommunication Switch
- Automatic Insertable
- Available in Ammo Pack
- Available on Radial Tape and Reel
- N-Channel, Small Signal, TMOS FET

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	60	Vdc
Drain–to–Gate Voltage (R_{GS} = 1 m Ω)	V _{DGR}	60	Vdc
Gate-to-Source Voltage	V _{GS}	40	Vdc
Drain Current Continuous Pulsed	I _D I _{DM}	150 1000	mAdc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	PD	400 3.2	mW mW/°C
Operating and Storage temperature Range	T _J , T _{stg}	–5.5 to +150	°C

THERMAL CHARACTERISTIC

Thermal Resistance Junction-to-Ambient	R_{\thetaJA}	312.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16 in from Case for 10 Seconds	ΤL	300	°C



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N-CHANNEL SMALL SIGNAL TMOS FET, $R_{DS(ON)} = 7.5 \Omega$, 60 V





2N7008

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characte	eristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain–to–Source Breakdown Voltage $(V_{GS} = 0, I_D = 100 \ \mu A)$		V _{(BR)DSS}	60	-	Vdc
Zero Gate Voltage Drain Current $(V_{DS} = 50 \text{ V}, V_{GS} = 0)$ $(V_{DS} = 50 \text{ V}, V_{GS} = 0, T_J = 125^{\circ}\text{C})$		I _{DSS}	-	1.0 500	μAdc
Gate-to-Body Leakage Current, Forward $(V_{GSF} = 30 \text{ Vdc}, V_{DS} = 0)$		I _{GSSF}	_	-100	nAdc
ON CHARACTERISTICS (Note 1)					
Gate Threshold Voltage (V _{DS} = V _{GS} , I_D = 250 m	A)	V _{GS(th)}	-	_	Vdc
$ Static Drain-to-Source On-Resistance \\ (V_{GS} = 5 Vdc, I_D = 50 mAdc) \\ (V_{GS} = 10 Vdc, I_D = 500 mA, T_C = 125 \\ $;°C)	R _{DS(ON)}	-	7.5 13.5	Ω
$ \begin{array}{l} \text{Drain-to-Source On-Voltage} \\ (\text{V}_{\text{GS}} = 5 \text{ V}, \text{ I}_{\text{D}} = 50 \text{ mA}) \\ (\text{V}_{\text{GS}} = 10 \text{ V}, \text{ I}_{\text{D}} = 500 \text{ mA}) \end{array} $		V _{DS(ON)}		1.5 3.75	Vdc
On–State Drain Current (V _{GS} = 10 V, V _{DS} \geq 2 V	(DS(ON))	I _{D(ON)}	500	-	mA
Forward Transconductance ($V_{DS} \ge 2 V_{DS(ON)}$,	_D = 200 mA)	9 _{FS}	80	-	μmhos
DYNAMIC CHARACTERISTICS					
Input Capacitance		C _{ISS}	-	50	pF
Output Capacitance	$V_{DS} = 25 V, V_{GS} = 0$ f = 1 MHz	C _{OSS}	-	25	1
Reverse Transfer Capacitance		C _{RSS}	-	5	1
SWITCHING CHARACTERISTICS (Note 1)					
Turn-on Delay Time	V _{DD} = 30 V, I _D = 200 mA	t _{ON}	-	20	ns
Turn–off Delay Time	$R_{GEN} = 25 \Omega, R_L = 150 \Omega$	t _{OFF}	_	20]

1. Pulse Test Pulse Width \leq 300 µs, Duty Cycle \leq 2%.



2N7008

PACKAGE DIMENSIONS







SECTION X-X

NOTES:

DIMENSIONING AND TOLERANCING PER ANSI 1. Y14.5M. 1982

CONTROLLING DIMENSION: INCH. CONTOUR OF PACKAGE BEYOND DIMENSION R

3

IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM. 4

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Η	0.095	0.105	2.42	2.66
L	0.015	0.020	0.39	0.50
Κ	0.500		12.70	
Г	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

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